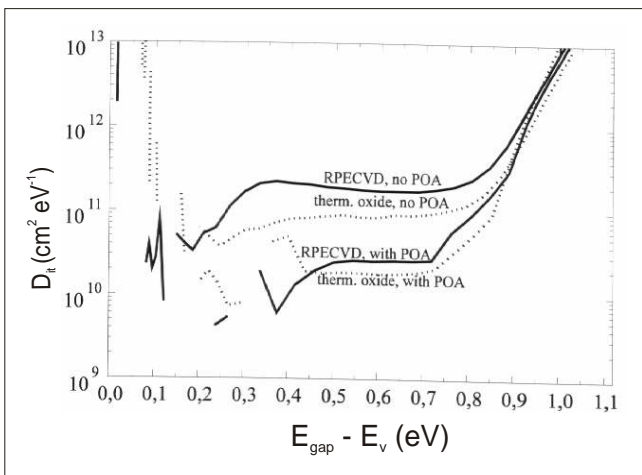
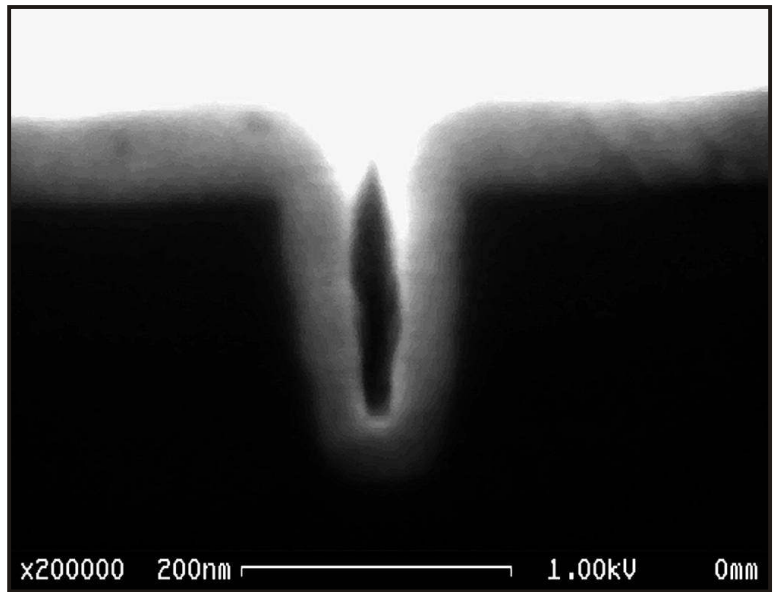
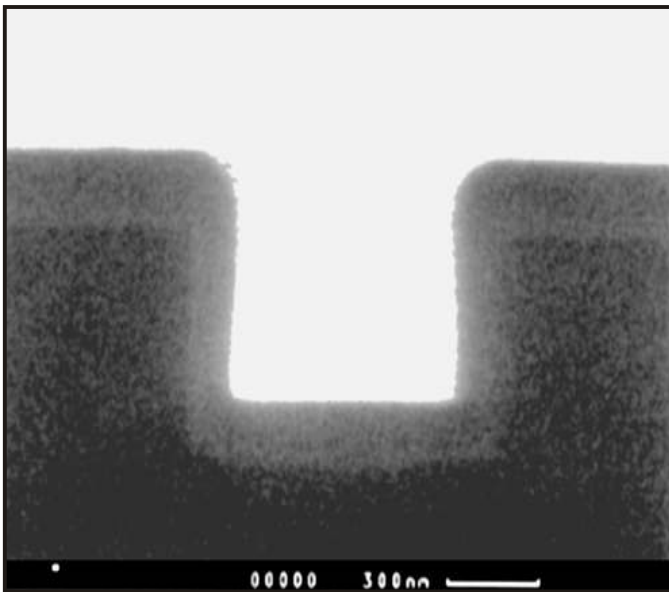




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Plasmalab Data

Very High Quality PECVD SiO₂ by ICP

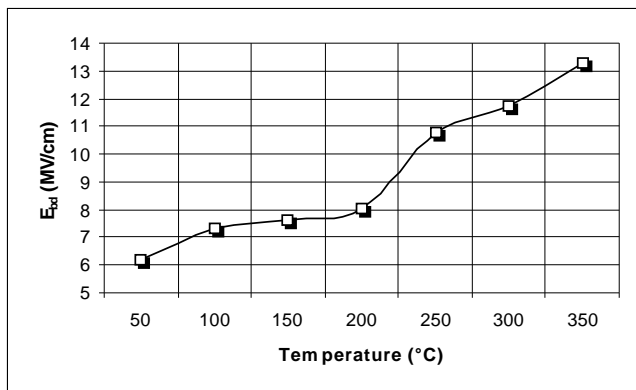


Courtesy of the RWTH Aachen Institut für Halbleitertechnik II, Prof. Kurz Contact J. Stein

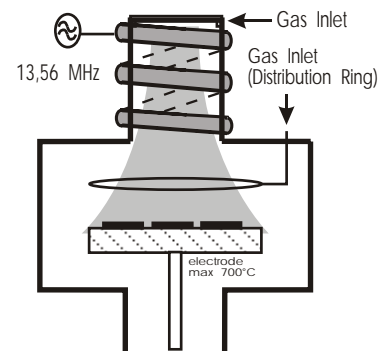
SEM's show the conformal deposition of 0.2 μm / 0.07 μm SiO₂ rate: 5 - 20 nm/ min uniformity over one wafer: +/- 4 %

Distribution of the interface state density D_{it} inside the band gap: remote PECVD SiO₂ vs thermal SiO₂ Post Anneal (POA) at 1050° C, 25 min N₂

- Plasmalab 80 Plus
- Plasmalab System 100
- Plasmalab System 133



Electrical Breakdown Field vs Deposition Temperature



Plasma Enhanced Chemical Vapour Deposition with (remote) Inductive Coupled Plasma source